TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII⁻⁵)

2SK1930

Chopper Regulator, DC–DC Converter, and Motor Drive Applications

- Low drain-source ON resistance $: RDS (ON) = 3.0 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 2.0 \text{ S} (typ.)$
- Low leakage current $: I_{DSS} = 300 \ \mu A \ (max) \ (V_{DS} = 800 \ V)$
- Enhancement mode $: V_{th} = 1.5 \sim 3.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	1000	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	1000	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	۱ _D	4	А	
	Pulse (Note 1)	I _{DP}	12	~	
Drain power dissipation (Tc = 25°C)		PD	100	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

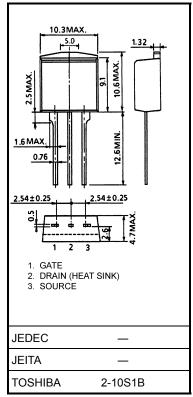
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

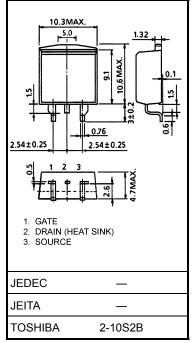
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch–c)}	1.25	°C / W
Thermal resistance, channel to ambient	R _{th (ch–a)}	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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Unit: mm

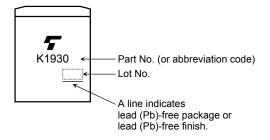
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	_	—	±100	nA
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 800 V, V _{GS} = 0 V		_	300	μA
Drain-source br voltage	rain-source breakdown $V_{(BR) DSS}$ $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$		1000	_	_	V	
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 2 A	_	3.0	3.8	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 20 V, I _D = 2 A	1.0	2.0	—	S
Input capacitance	ce	C _{iss}		_	700	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		55	_	pF
Output capacitance		C _{oss}			100	_	
Switching time	Rise time	tr	$v_{GS} \stackrel{10V}{}_{0V} \prod_{U \\ C \\ $	_	18	_	- ns
	Turn-on time	t _{on}		_	30	_	
	Fall time	t _f		_	12	_	
	Turn-off time	toff	V_{DD} ≒400V Duty ≦1%, t _w =10µs	_	70	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	60	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 4 A		35	_	nC
Gate-drain ("miller") charge		Q _{gd}			25	_	

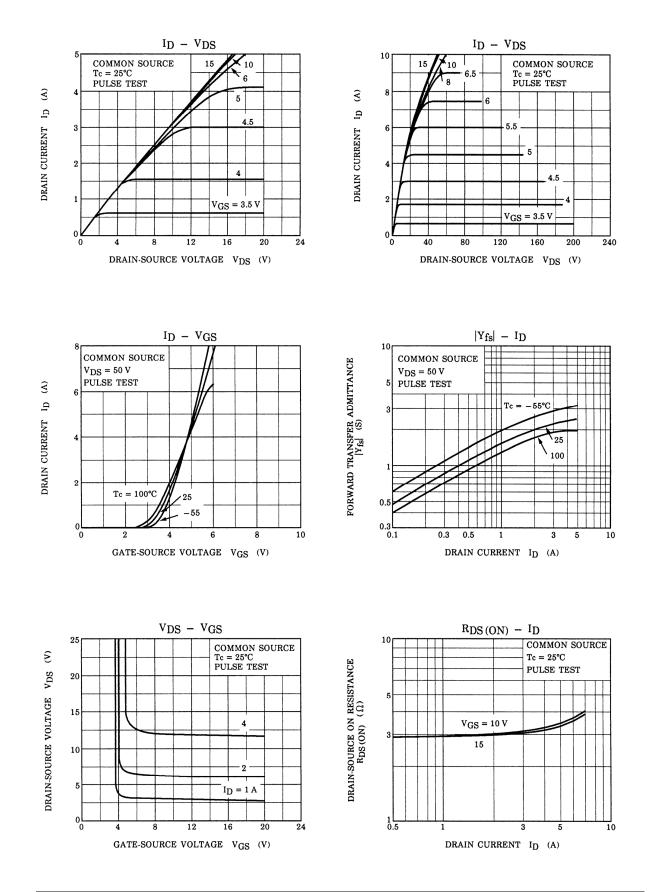
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	4	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	12	A
Forward voltage (diode)	VDSF	I _{DR} = 4 A, V _{GS} = 0 V			-1.9	V

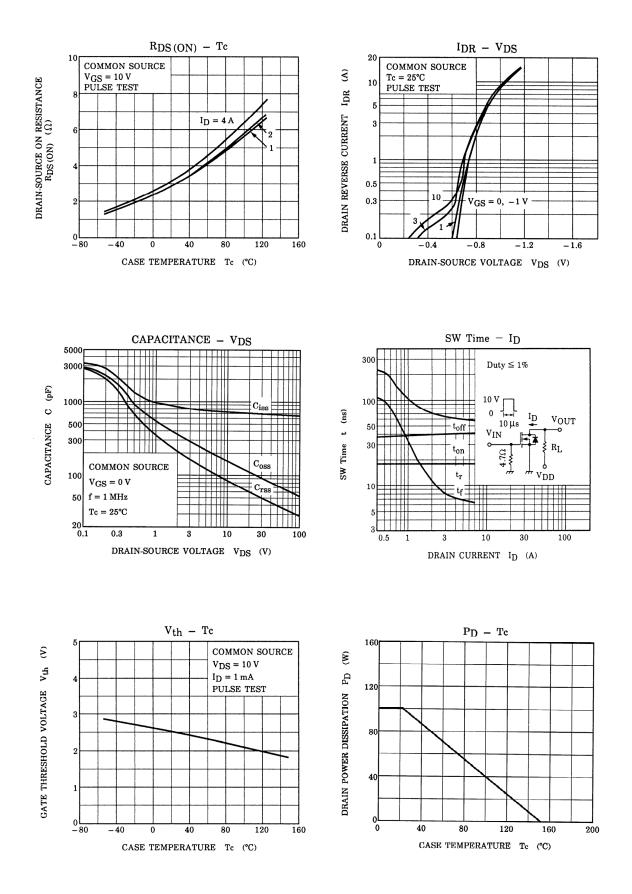
Marking

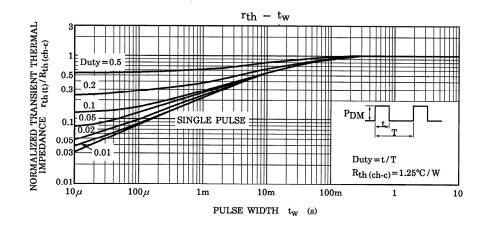


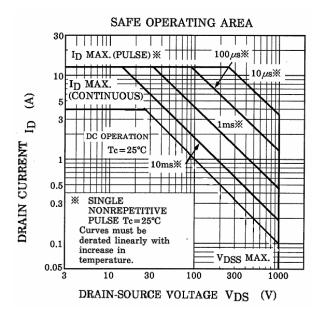
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